Standard specifications of 10×15 mm² β-Ga₂O₃ epitaxial wafer (by MBE)

Epitaxial layer

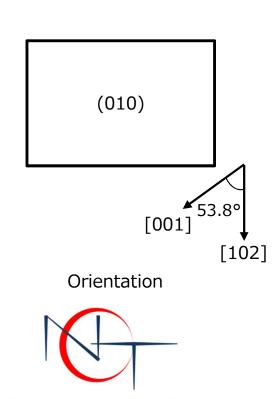
Items	Specifications	
Dopant	Si (n-type)	Undoped (semi-insulating)
Doping concentration *A value can be selected within the described range.	Specify a value in the range between 1×10^{17} and 2×10^{18} cm ⁻³	-
Thickness *A value can be selected within the described range.	Specify a value in the range between 0.1 and 0.5 µm	

β-Ga ₂ O ₃ epitaxial layer	
β-Ga ₂ O ₃ wafer	

Cross section of β -Ga₂O₃ epitaxial wafer

Wafer

Items	Specifications	
Dopant	Sn (n-type)	Fe (semi-insulating)
Doping concentration	Using the range of $1\sim 9{ imes}10^{18}{ m cm}^{-3}$	-
Resistivity	-	≧10 ¹⁰ Ωcm
Orientation	(010)	
Size	10×15 mm ²	
Thickness	0.5 mm	
XRD FWHM	≦150 arcsec	
Off set angle	0°±1°	



Remarks

- 1 These products must be used for research and development purposes only.
- 2 The substrates must not be used as a seed crystal.
- 3 The specifications are subject to change without notice.